UNIT III

BJT AMPLIFIERS

BJT h-parameter model

Analysis of transistor amplifier using h-parameter model

CB, CE and CC amplifiers

Comparison of CB, CE and CC configurations

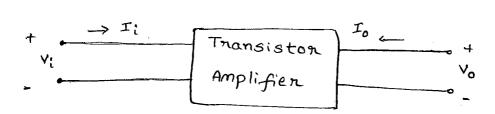
Simplified h-parameter model



BJT AMPLIFIERS

H-Panameter Representation of a Transiston

A transistor can be treated as a two-port Network



Hene Ii = Input connent to the Amplifier

Vi = Input voitage to the Amplifier

To = output connent of the Amplifier

Vo = output voitage of the Amplifien

Transistor is a current operated device.

Here input voltage Vi and output current Io are the dependent variables.

Input current Ii and output voitage vo are Independent variables.

$$V_i = f_1(T_1, V_0)$$

$$T_0 = f_2(T_i, V_0)$$

This can be written in the equation form as follows

$$V_i = h_{i1} T_i + h_{i2} V_0$$

$$I_0 = h_{21} I_i + h_{22} V_0$$

the above equation can also be written using alphabetic notations

$$V_{i} = h_{i} T_{i} + h_{n} V_{0}$$

$$T_{0} = h_{f} T_{i} + h_{0} V_{0}$$

Definitions of h-parameter:

The parameters in the above equation are defined as follows

$$h_{ii} = h_i = \frac{V_i}{T_i} \bigg|_{V_0 = 0}$$
 = Input mesistance with output Short circuited.

$$h_{12} = h_n = \frac{V_i}{I_0} \Big|_{I_i=0}$$
 = Revense voitage transfer nation with input open circuited.

$$h_{21} = h_f = \frac{T_0}{T_i} \Big|_{V_0=0} = \frac{\text{Short cincuit} \times \text{current gain}}{\text{with output short cincuited}}$$

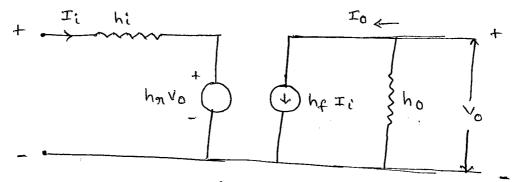
$$h_{22} = h_0 = \frac{I_0}{V_0} \Big|_{I_1 = 0} = \begin{array}{c} \text{output Admittance with input} \\ \text{open cincuited.} \end{array}$$

BJT H-panameter model:

Based on the definition of hybrid parameters the mathematical model for two port networks known as h-parameter model (Hybrid Parameter model) can be developed.

The two equations of a transiston is given by $V_i = h_i \, T_i \, + \, h_n \, V_0$ $T_0 = h_f \, T_i \, + \, h_0 \, V_0$

Based on above two equations the equivalent circuit on Hybrid Model for transistor can be drawn.

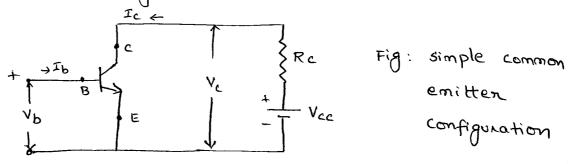


Advantages (on) Benifits of h- panameters

- 1) Real numbers at audio frequencies
- 2) Easy to measure
- 3) can be obtained from the transistor static chanacteristic conves.
- 4) convinient to use in circuit analysis and design.
- 5) Easily convertable from one configuration to other
- 6) most of the transistor manufacturers sepecify the h-parameters.

H panameten model for CE configuration

Let us consider the common emitter configuration shown in figure below. The Vaniables Ib, Ic, Vb and Vc nepnesent total instantaneous connents and Voltages.

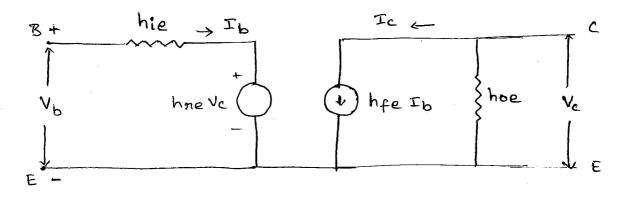


emitten Configuration

Here Ib - Input corrent Vb - Input Voltage

Ic - output current Vc - output voitage

h- parameter model for common emitter configuration shown in figure below.

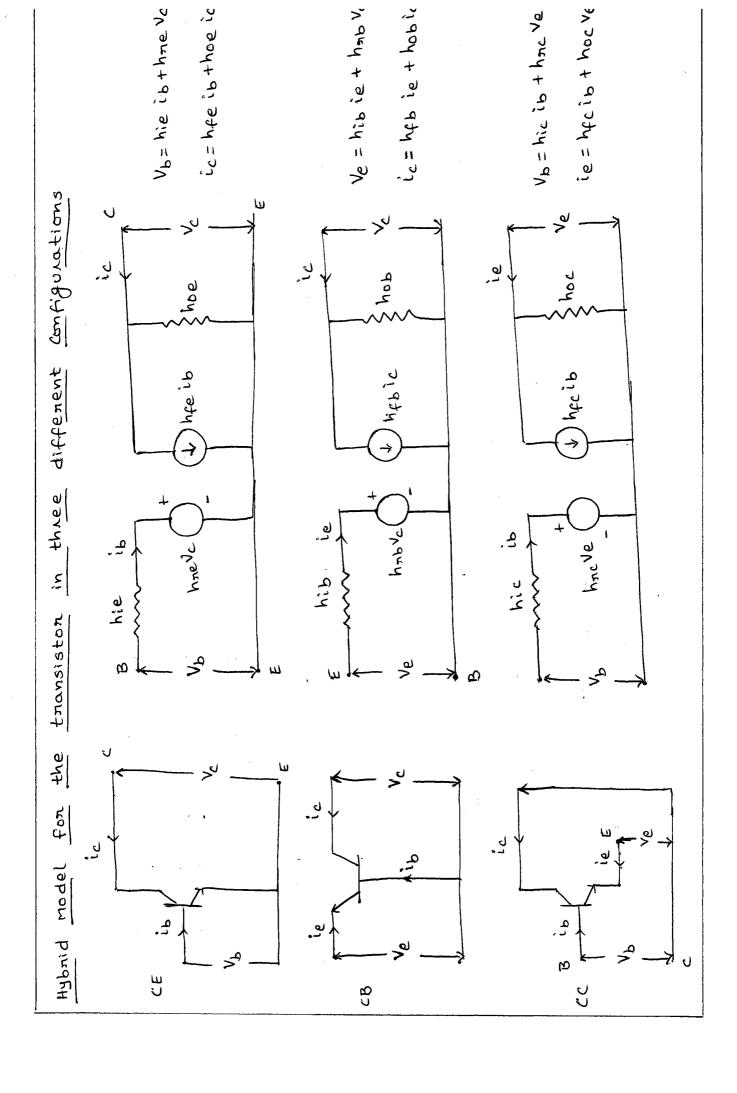


where hie =
$$\frac{\Delta V_B}{\Delta I_B}$$
 | $V_c = constant$ = $\frac{V_b}{I_b}$ | $V_c = constant$

hne =
$$\frac{\Delta V_B}{\Delta V_C}$$
 | $I_B = Constant$ = $\frac{V_b}{V_c}$ | $I_b = Constant$

here =
$$\frac{\Delta T_c}{\Delta T_B}$$
 | $V_c = Constant$ = $\frac{ic}{ib}$ | $V_c = Constant$

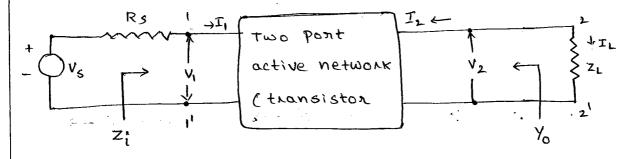
$$hoe = \frac{\Delta I_c}{\Delta V_c}$$
 $I_B = constant = \frac{i_c}{V_c}$
 $I_b = constant$



Typical h-parameter values for a transistor				
Panameten 2	CE	cc	cB	
hi	1100 L	11001	22 N	
hn	25 x 10-4	1	3 × 10 4	
her 9	50	-51	-0198	
ho	25 MA/V	25 MA/V	0.49 MA/V	

Analysis of a transiston amplifien cincuit using h-panameter model.

A transistor amplifier can be constructed by connecting an external load and signal source as indicated in figure below and biasing the transistor properly.



The hybrid parameter model for above network is shown in figure below.

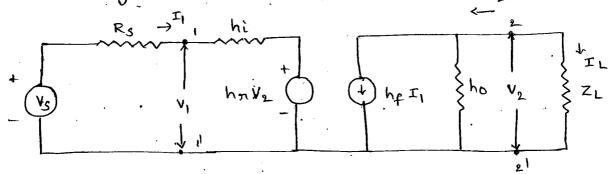


Fig: transiston hybrid parameter model.

Connent Gain (on) Connent Amplification A:

For a transistor amplifier the connent gain $A_{\rm I}$ is defined as the natio of output corrent to input corrent.

$$A_{I} = \frac{I_{L}}{I_{I}} = \frac{-I_{2}}{I_{I}}$$

From the circuit $I_2 = h_f I_1 + h_0 V_2 \longrightarrow 0$ $V_2 = I_L Z_L = -I_2 Z_L \longrightarrow 0$

Sub 2 in 0

$$I_2(1+Z_Lh_0) = hf I_1 \Rightarrow \frac{I_2}{I_1} = \frac{hf}{1+Z_Lh_0}$$

$$A_{I} = \frac{-I_{2}}{I_{1}} = \frac{-hf}{1+Z_{L}ho}$$

AI

Input Impedance zi

In the circuit Rs is the signal source resistance the impedance seen when looking in to the amplifien terminals (1,1') is the amplifier input impedance z_i

$$Z_i = \frac{V_i}{I_i}$$

From figure $V_1 = h_1 I_1 + h_n V_2$

So
$$Z_{i} = \frac{h_{i} I_{1} + h_{n} V_{2}}{I_{1}} = h_{i} + h_{n} \frac{V_{L}}{I_{1}} \rightarrow 0$$

$$V_{2} = -I_{2} Z_{L} = A_{I} I_{1} Z_{L} \qquad \left(\begin{array}{c} A_{I} = -\frac{I_{2}}{I_{1}} \end{array} \right)$$

$$Z_{i} = h_{i} + h_{n} \frac{A_{I} I_{1} Z_{L}}{I_{1}}$$

$$Z_{i} = h_{i} + h_{n} A_{I} Z_{L}$$

$$Z_{i} = h_{i} - h_{n} A_{I} Z_{L}$$

$$Z_{i} = h_{i} - \frac{h_{f} h_{n}}{I + h_{0}} Z_{L}$$

$$Z_{i} = h_{i} - \frac{h_{f} h_{n}}{I_{L} + h_{0}}$$

$$Z_{i} = h_{i} - \frac{h_{f} h_{n}}{V_{L} + h_{0}} \qquad \left(\begin{array}{c} A_{L} = \frac{I_{L}}{I_{L}} \end{array} \right)$$

$$Z_{i} = h_{i} - \frac{h_{f} h_{n}}{V_{L} + h_{0}} \qquad \left(\begin{array}{c} A_{L} = \frac{I_{L}}{I_{L}} \end{array} \right)$$

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$$Z_{i} = h_{i} - \frac{h_{f} h_{n}}{V_{L} + h_{0}} \qquad \left(\begin{array}{c} A_{L} =$$

The natio of output voltage V2 to input voltage gives the voitage gain of the transistor

$$A_V = \frac{V_2}{V_1}$$

Substituting V2 = - I2 ZL = AI I1 ZL

$$\Rightarrow AV = \frac{AII_1ZL}{V_1} = \frac{AIZL}{V_1/I_1} = \frac{AIZL}{Zi}$$

4) output Admittance (Yo):

$$V_0 = \frac{\Gamma_2}{V_2}$$
 with $V_S = 0$ and $R_L = \infty$

From the circuit $I_2 = h_f I_1 + h_0 Y_2$

Dividing by
$$V_2$$
, $\frac{I_2}{V_2} = h_f \frac{I_1}{V_2} + h_0 \longrightarrow 0$

with Vs = 0, by KVL in input cincuit

$$I_1\left(R_S+h_i\right)+h_n\,V_2=0$$

Hence
$$\frac{I_1}{V_2} = \frac{h_n}{R_s + h_i}$$

NOW Eq
$$0 \Rightarrow \frac{T_2}{V_2} = \frac{-h_f h_n}{R_S + h_i} + h_0$$

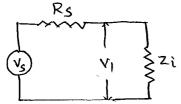
$$\Rightarrow y_0 = h_0 - \frac{h_f h_n}{R_s + h_i}$$

CE

CC

5) Voltage gain (Avs) (Including sounce):

$$A_{VS} = \frac{V_2}{V_S} = \frac{V_2}{V_1} \frac{V_1}{V_S} \Rightarrow A_{VS} = A_V \frac{V_1}{V_S}$$



$$V_1 = \frac{V_s z_i}{R_s + z_i} \implies \frac{V_1}{V_s} = \frac{z_i}{R_s + z_i}$$

NOW
$$A_{VS} = \frac{A_V Z_i}{R_S + Z_i}$$

$$A_{VS} = \frac{A_{I} R_{L}}{2i} \times \frac{Z_{i}}{R_{S} + Z_{i}} = \frac{A_{I} R_{L}}{R_{S} + Z_{i}}$$

If
$$R_s = 0$$
 then $A_{VS} = \frac{A_{IRL}}{Z_{I}} = A_{V}$.

6) corrent Amplification (AIS)

$$A_{\text{IS}} = \frac{-I_2}{I_S} = \frac{-I_2}{I_1} \cdot \frac{I_1}{I_S} = A_{\text{I}} \cdot \frac{I_1}{I_S}$$

The modified input cincuit using Nonton's equivalent cincuit for the sounce for the calculation of AIS

$$A_{IS} = A_{I} \frac{R_{S}}{R_{S} + Z_{i}}$$

$$\begin{array}{c|c}
 & \rightarrow & I_1 \\
\hline
 & & & & &$$

=) In CE configuration

$$\left(Z_{L} = R_{L} \right)$$

Input Impedance
$$z_i = hie - \frac{hfehne}{Y_L + hoe} \left(Y_L = \frac{1}{Z_L} = \frac{1}{R_L} \right)$$

=) In CB configuration

Input Impedance
$$z_i = hib - \frac{hfb hnb}{Y_L + hob}$$

output Admittance
$$y_0 = h_{0b} - \frac{h_{fb} h_{nb}}{h_{ib} + R_s}$$

Voitage gain
$$AV = \frac{A_{I} Z_{L}}{Z_{i}}$$

Convension formulae for hybrid parameters

CB > CC

$$hib = \frac{hie}{1 + hfe}$$

$$h_{fb} = \frac{-h_{fe}}{-h_{fe}}$$

$$h_{ob} = \frac{h_{oe}}{1 + h_{fe}}$$

- 1) characteristics of common emitter Amplifier
 - 1) Current gain AI is high for RL < 10 Kr
 - 2) the voitage gain is high for normal values of Load nesistance RL
 - 3) The input nesistance Ri is medium
 - 4) the output resistance Ro is moderately high

Applications of common emitter amplifier:

2)

- of the three configurations ce amplifier alone is capable of providing both voltage gain and current gain.
- 2. The output nesistance Ro and input nesistance Ri are moderately high
- 3. CE amplifien is widely used for Amplification purpose chanacteristics of common Base Amplifien:
- 1. Current gain is less than unity and its magnitude decreases with the increase of load resistance RL
- 2. Voitage gain Av is high for normal values of RL
- 3. The input nesistance Ri is the lowest of all the three configurations.
- 4. The output resistance Ro is the highest of all the three configurations.

Applications of common base Amplifier

The CB Amplifien is not commonly used for Amplification purpose. It is used for

- 1) matching a very low impedance source.
- 2) As a non inventing amplifien with voltage gain exceeding unity
- 3) For driving a high impedance load
- 4) As a Constant current sounce.
- 3) characteristics of common collector Amplifier

 1 For low value of RL (< 10K1) The comment gain Ax is

 high and almost equal to that of a CE amplifier

- 2. The voltage gain Av is less than unity.
- 3. The input resistance is the highest of all the three configurations.
- 4 The output nesistance is the lowest of all the three configurations.

Applications of common collector Amplifier:

the cc Amplifier is widely used as a buffer stage between a high impedance source and low impedance load. (cc Amplifier is called emitter follower)

the characteristics of three configurations are summarized in table below Here the quantities AI, AV, Ri, Ro and Ap (Power gain) are calculated

for $R_L = R_S = 3 K \Lambda$

quantity	CB	CC	CE .
Ar	0.98	47.5	-46,5
Av	131	0.989	-131
Δ _D	128.38	46.98	6091.5
Ap R:	22.6 ∧	144 KA	1065 N
Ro	1.72MA	80.5A	45.5 KN

Simplified CE Hybrid model (on) Approximate CE
Hybrid model (Approximate Analysis):

As the h parameters themselves vary widely for the same type of transistor. It is justified to make approximations and simplify the expressions for AI, AV, AP, Ri and Ro.

The behaviour of the transistor circuit can be obtained by using the simplified hybrid model. The h-parameter equivalent circuit of the transistor in the ce configuration is shown in figure below.

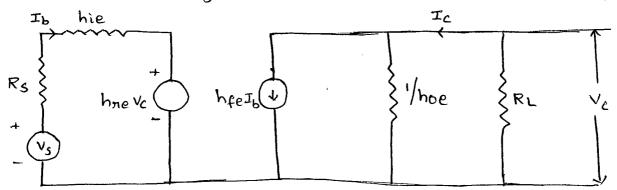


Fig: Exact ce Hybrid model.

Here is in parallel with RL

The panallel combination of two onequal impedances is approximately equal to the lower value in Ri. Hence if $\frac{1}{hoe}$ >> Ri, then the term how may be neglected how provided that how Ri << 1 and 1 and

generated in the emitter circuit is

hne $|V_c|$ = hne I_c R_L = hne hee I_b R_L Since hne hee \approx 0.01, this voltage may be neglected in companison with the voltage drop across hie ie hie I_b provided that R_L is not too large ie g_t the load mesistance R_L is small it is possible to neglect the parameter hne and hoe and the approximate equivalent cincuit is obtained as shown in figure below.

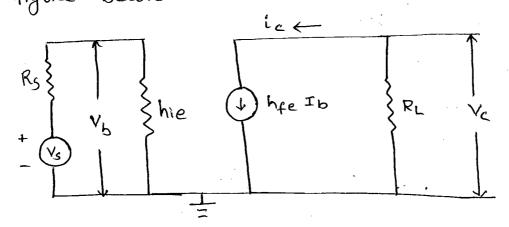


Fig: Approximate cE Hybrid model.

1) CULLENT Gain (AI):

The current gain for CE configuration is

$$A_{I} = \frac{-hfe}{1 + hoe R_{L}}$$
, of hoe RL < 0.1

$$A^{I} = -\mu t \delta$$

2) Input Impedance (Z1):

By exact analysis
$$Z_i = R_i = \frac{V_i}{T_i}$$

$$V_{1} = hie I_{1} + hne V_{2}$$

$$Z_{1} = \frac{hie I_{1} + hne V_{2}}{I_{1}} = hie + hne \frac{V_{2}}{I_{1}}$$

$$V_{2} = -I_{2}Z_{L} = -I_{2}R_{L} = A_{I}I_{1}R_{L} \qquad \left(\begin{array}{c} \cdot \cdot A_{I} = -I_{2} \\ -I_{2} \end{array} \right)$$

$$Z_{1} = hie + hne \frac{A_{I}I_{1}R_{L}}{I_{1}} \qquad \left(\begin{array}{c} \cdot \cdot V_{L} = A_{I}I_{1}R_{L} \\ -I_{2} \end{array} \right)$$

$$R_{1} = hie + hne A_{I}R_{L}$$

$$R_{1} = hie \left(\begin{array}{c} 1 + \frac{hne A_{I}R_{L}}{hie} \\ -hie \end{array} \right)$$

$$R_{1} = hie \left(\begin{array}{c} 1 + \frac{hne A_{I}R_{L}}{hie} \\ -hie \end{array} \right)$$

$$Vsing the typical values for the h-parameters$$

$$\frac{hne hie}{hie hoe} \approx 0.5$$

$$hie hoe$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 + \frac{0.5 A_{I}R_{L}}{hoe} \\ -he R_{L} \end{array} \right)$$

$$We know that A_{I} = \frac{-hfe}{1 + hoe}R_{L}$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{0.5 hfe}{he}R_{L} \\ -he R_{L} \end{array} \right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{0.5 hfe}{he}R_{L} \\ -he R_{L} \end{array} \right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{0.5 hfe}{he}R_{L} \\ -he R_{L} \end{array} \right)$$

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$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{0.5 hfe}{he}R_{L} \\ -he R_{L} \end{array} \right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{0.5 hfe}{he}R_{L} \\ -he R_{L} \end{array} \right)$$

then Ri = hie

voitage gain:
$$A_V = A_I \frac{R_L}{R_i} = -\frac{h_f e}{h_i e}$$

Output Impedance:

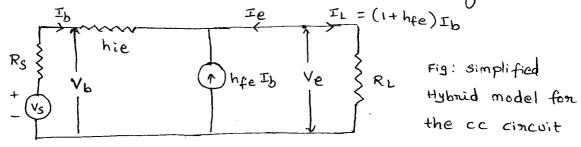
It is the natio of V_c to I_c with $V_s=0$ and R_L excluded. The simplified cincuit has infinite output impedance because with $V_s=0$ and external voltage sounce applied at output, it is found that $I_b=0$ and hence $I_c=0$

$$R_0 = \frac{V_c}{I_c} = \infty \quad \left(:: I_c = 0 \right)$$

Approximate analysis of CE Amplifier connent gain AI = -hfeInput resistance $R_i = hie$ Voltage gain $AV = \frac{-hfe}{hie}$ Output resistance $R_0 = \infty$

Analysis of cc Amplifier using the approximate Model:

Figure shows the equivalent cincuit of cc Amplifications using the approximate model with the collector grounded, input signal applied between base and ground and load connected between emitter and ground.



$$A_{I} = \frac{I_{L}}{I_{b}} = \frac{\left(1 + hfe\right)I_{b}}{I_{b}} = \left(1 + hfe\right)$$

2) Input nesistance

$$R_i = \frac{V_b}{I_h} = h_{ie} + (1 + h_{fe}) R_L$$

3) Voltage gain

$$Av = \frac{Ve}{V_b} = \frac{(1+hfe) I_b R_L}{\left(h_{ie} I_b + (1+hfe) I_b R_L\right)}$$

$$A_{V} = \frac{(i+h_{fe})R_{L}}{h_{ie} + (i+h_{fe})R_{L}} = \frac{h_{ie} + (i+h_{fe})R_{L} - h_{ie}}{h_{ie} + (i+h_{fe})R_{L}}$$

$$Av = 1 - \frac{hie}{hie + (1+hfe)RL}$$

$$A_V = 1 - \frac{hie}{Ri}$$
 (", Ri = hie + (1+hfe)RL)

4) Output Impedance !-

short circuit coment
in output terminals =
$$(1+hfe)$$
 $Tb = (1+hfe)$ Vs
 R_1+hio

$$Y_0 = \frac{1 + hfe}{Rs + hie} \Rightarrow R_0 = \frac{hie + Rs}{1 + hfe}$$

Analysis of CB Amplifier using the approximate model

Figure shows the equivalent cincuit of CB amplifien using the approximate model, with the base grounded, input signal is applied between emitten and base and load connected between collector and base

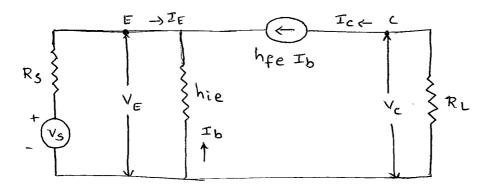


Fig: Simplified Hybrid model for the CB circuit

i) corrent gain!

From the figure above
$$A_{\rm I}=\frac{-{\rm I}_{\rm C}}{{\rm I}_{\rm E}}=\frac{-\,{\rm hfe}\;{\rm I}_{\rm b}}{{\rm I}_{\rm E}}$$

$${\rm I}_{\rm E}=-\left(\,{\rm I}_{\rm b}+{\rm I}_{\rm C}\right)$$

$${\rm I}_{\rm E}=-\left(\,{\rm I}_{\rm b}+{\rm hfe}\;{\rm I}_{\rm b}\right)=-\left(\,{\rm I}_{\rm hfe}\right)\,{\rm I}_{\rm b}$$

$${\rm A}_{\rm I}=\frac{-{\rm hfe}\;{\rm I}_{\rm b}}{-\left(\,{\rm I}_{\rm hfe}\right)\,{\rm I}_{\rm b}}=\frac{{\rm hfe}}{{\rm I}_{\rm hfe}}=-{\rm hfb}$$

2) Input Resistance:

Input Resistance
$$R_i = \frac{Ve}{Te}$$

From figure $Ve = -Tbhie$, $Te = -(1+hfe)Tb$
 $R_i = \frac{hie}{1+hfe} = hib$

3) voitage gain:

$$A_V = \frac{V_C}{Y_C}$$

$$V_{c} = -I_{c}R_{L} = -h_{f}e I_{b}R_{L}$$

$$V_{e} = -I_{b} h_{i}e$$

$$A_{V} = \frac{h_{f}e R_{L}}{h_{i}e}$$

output Impedance

$$R_0 = \frac{V_c}{I_c}$$
 with $V_{S=0}$, $R_L = \infty$

with
$$V_s=0$$
, $I_e=0$ and $I_b=0$ hence $I_c=0$

$$\therefore R_0 = \frac{V_C}{0} = \infty$$

Approximate Analysis of CB Amplifier

Approximate Analysis of CC Amplifier

3) Voitage gain
$$AV = I - \frac{hie}{Ri}$$

<u>Problem</u>: A CE Amplifier is drawn by a Voltage source of Internal mesistance 9s=800 and the load impedance is a mesistance $R_L=1000$ Ω . The h parameters are hie= $1\kappa\Omega$, hre= 2×10^4 , hfe=50 and hoe= 25μ A/V. compute the current gain AI, input Mesistance R_i , Voltage gain AV, and output Mesistance R_0 using exact analysis and approximate analysis.

solution! Given data

91s=800 Ω , $R_L=1000$ Ω , hie=1k Ω , hae=2×10⁻⁴ , hfe=50 , and hoe=25 μ A/V

Exact Analysis: -

Input Resistance $R_i = h_{ie} - \frac{h_{fe} h_{ne}}{h_{oe} + \frac{1}{R_L}} = 990.24 \text{ n}$

Voltage gain $A_V = A_I \frac{R_L}{R_i} = -49.26$

output Resistance

$$y_0 = h_0e - \frac{h_fe h_ne}{h_ie + R_s} = 194 \times 10^{-5} \text{ mho}$$

$$R_0 = \frac{1}{y_0} = 51.42 \text{ K} \Lambda$$

Approximate Analysis:

$$A_{I} = -hfe = -50$$

Ri = hie = 1 kn

$$Av = \frac{-hfe RL}{hie} = \frac{-50 \times 1000}{1000} = -50$$

Problem! A voitage source of Internal nesistance $R_s = 900 \text{ A}$ drives a cc amplifier using load resistance $R_L = 2000 \text{ A}$. The CE h-banameters are hie = 1200 \textstance, hre = 2x10⁻⁴, hre = 60 and hoe = 25 \textstance R_i, voitage gain Av, and output nesistance Ro using exact analysis and approximate analysis.

$$h_{fc} = -(1 + h_{fe}) = -(1 + 60) = -61$$

Exact Analysis:

$$A_{I} = \frac{-hfc}{-hoc} = 58.095$$

$$1 + hoc R_{L}$$

$$R_i = hic - \frac{hfc hnc}{Y_L + hoe} = 117.39 KM$$

$$A_V = \frac{A_I R_L}{R_1^2} = 0.9897$$

output Admittance

$$\Rightarrow$$
 Ro = $\frac{1}{y_0}$ = 34.396 Λ

Approximate Analysis

$$A_V = 1 - \frac{hie}{Ri} = 0.99$$

$$R_0 = \frac{\text{hie} + R_S}{1 + \text{hfe}} = 34.43 \text{ } \Lambda$$

Problem:

For a CB transiston Amplifier driven by a voltage sounce of internal Mesistance Rs = 12001, the load impedance is a Mesiston RL = 10001. The h-parameters are hib = 221, hnb = 3×10⁴, hfb = -0.98, hob = 0.544/v. Compute the current gain AI, Input impedance Ri, Voltage gain Av, overall voltage gain Avs, over all Current gain AIs, output impedance Ro and power gain Ap using exact and approximate analysis.

solution:

Voitage gain
$$AV = \frac{AIRL}{R_1} = \frac{0.98 \times 1000}{22.3} = 43.94$$

overall Voitage gain Avs =
$$\frac{AvRi}{Ri + Rs}$$
 = 0.802

overall convent gain AIS =
$$\frac{AIRs}{Ri+Rs}$$
 = 0.962

$$R_0 = \frac{1}{Y_0} = 1.35 \,\text{MA}$$

Approximate Analysis:

$$\frac{1}{1}$$
) AI = -\text{ptp} = 0.48

$$AV = \frac{49 \times 1000}{1100}$$

$$(A)$$
 $R_0 = \infty$

Avs, AIs, AP are same as that of Exact analysis.

$$h_{fb} = \frac{-h_{fe}}{h_{fb}}$$

$$\Rightarrow hfe = \frac{-hfb}{-hfb} = 49$$